

## DB101-G Thru. DB107-G

Reverse Voltage: 50 to 1000V

Forward Current: 1.0A

RoHS Device



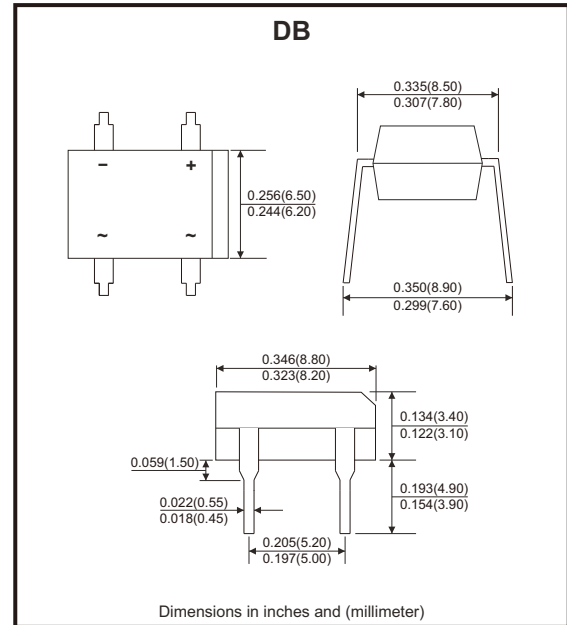
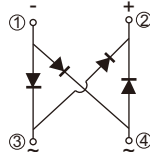
### Features

- Glass passivated chip.
- High surge forward current capability.
- Reliable low cost construction utilizing molded plastic technique.
- Lead in plated copper.
- UL recognized file # E349301 

### Mechanical Data

- Case: DB, molded plastic.
- Polarity: Symbol marked on body.
- Mounting position: Any.

### Circuit Diagram



### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%

| Parameter                                                                                                               | Symbol          | DB 101-G    | DB 102-G | DB 103-G | DB 104-G | DB 105-G | DB 106-G | DB 107-G | Unit               |
|-------------------------------------------------------------------------------------------------------------------------|-----------------|-------------|----------|----------|----------|----------|----------|----------|--------------------|
| Maximum repetitive peak reverse voltage                                                                                 | $V_{RRM}$       | 50          | 100      | 200      | 400      | 600      | 800      | 1000     | V                  |
| Maximum RMS voltage                                                                                                     | $V_{RMS}$       | 35          | 70       | 140      | 280      | 420      | 560      | 700      | V                  |
| Maximum DC blocking voltage                                                                                             | $V_{DC}$        | 50          | 100      | 200      | 400      | 600      | 800      | 1000     | V                  |
| Maximum average forward rectified current @ $T_A=40^\circ\text{C}$                                                      | $I_{AV}$        | 1.0         |          |          |          |          |          |          | A                  |
| Peak forward surge current, 8.3ms single half sine-wave, superimposed on rated load (JEDEC method)                      | $I_{FSM}$       | 30          |          |          |          |          |          |          | A                  |
| $I^2t$ rating for fusing ( $t < 8.3\text{ms}$ )                                                                         | $I^2t$          | 3.7         |          |          |          |          |          |          | A <sup>2</sup> s   |
| Peak forward voltage per diode at 1.0A DC                                                                               | $V_F$           | 1.1         |          |          |          |          |          |          | V                  |
| Maximum DC reverse current at rated @ $T_J=25^\circ\text{C}$<br>DC blocking voltage per diode @ $T_J=125^\circ\text{C}$ | $I_R$           | 10<br>500   |          |          |          |          |          |          | $\mu\text{A}$      |
| Typical junction capacitance (Note 1)                                                                                   | $C_J$           | 25          |          |          |          |          |          |          | pF                 |
| Typical thermal resistance junction to ambient (Note 2)                                                                 | $R_{\theta JA}$ | 40          |          |          |          |          |          |          | $^\circ\text{C/W}$ |
| Operating junction temperature range                                                                                    | $T_J$           | -55 to +150 |          |          |          |          |          |          | $^\circ\text{C}$   |
| Storage temperature range                                                                                               | $T_{STG}$       | -55 to +150 |          |          |          |          |          |          | $^\circ\text{C}$   |

Notes: 1. Measured at 1MHz and applied reverse voltage of 4V DC.  
2. Thermal resistance from junction to ambient mounted on P.C.B, with 0.5x0.5"(13x13mm) copper pads.  
3. The typical data above is for reference only.

## Rating and Characteristics Curves (DB101-G Thru. DB107-G)

Fig.1 - Forward Current Derating Curve

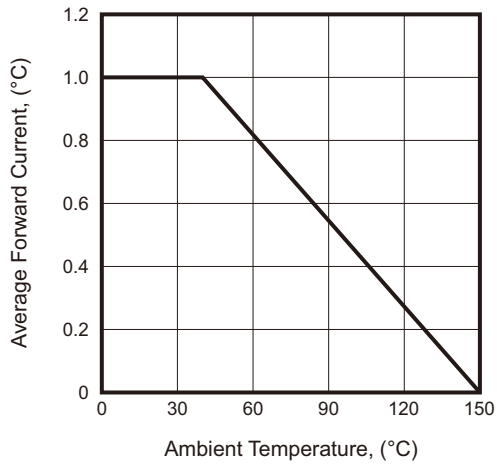


Fig.2 - Maximum Non-Repetitive Surge Current

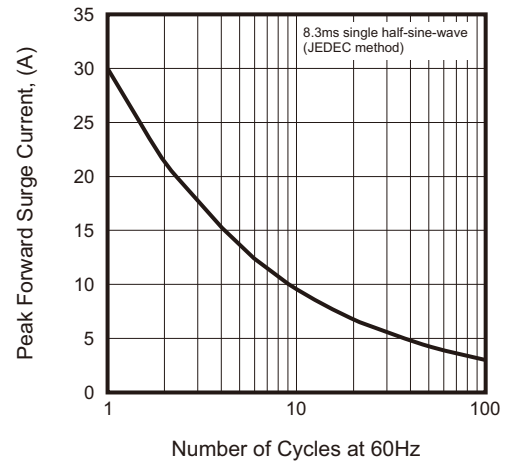


Fig.3 - Typical Reverse Characteristics

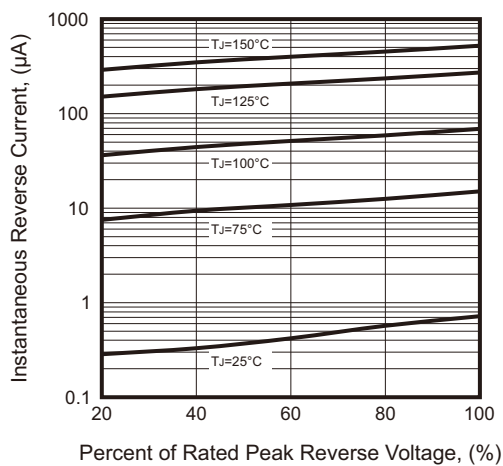


Fig.4 - Typical Forward Characteristics

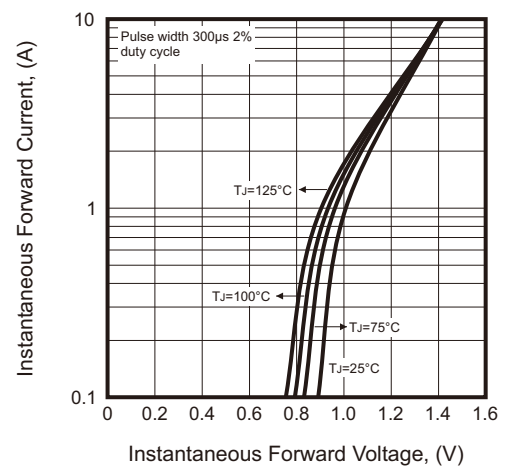
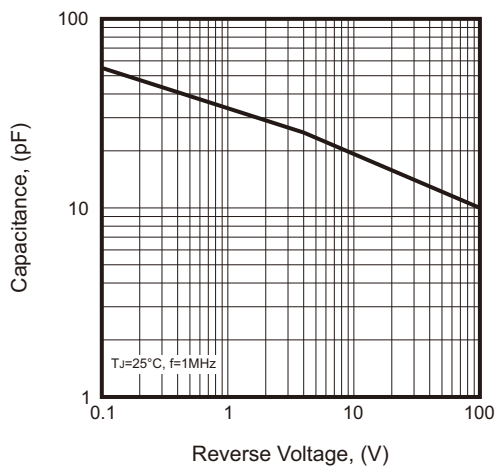
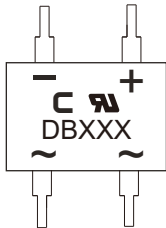


Fig.5 - Typical Junction Capacitance



## Marking Code

| Part Number | Marking code |
|-------------|--------------|
| DB101-G     | DB101        |
| DB102-G     | DB102        |
| DB103-G     | DB103        |
| DB104-G     | DB104        |
| DB105-G     | DB105        |
| DB106-G     | DB106        |
| DB107-G     | DB107        |



XXX = Product type marking code  
C = Comchip Logo

## Standard Packaging

| Case Type | TUBE PACK       |                |
|-----------|-----------------|----------------|
|           | TUBE<br>( pcs ) | BOX<br>( pcs ) |
| DB        | 50              | 2,500          |